7.5±0.2

Unit: mm

4.5±0.2

2SC4545

Silicon NPN epitaxial planar type

For medium output power amplification

Features

• Allowing supply with the radial taping

Absolute Maximum Rating	s $T_a = 2$	5°C			6.0 ±1.0	0.7±0.1 1.15±0.2	0.7±0.1	
Parameter	Symbol	Rating	Unit		-		1.15±0.2	
Collector-base voltage (Emitter open)	V _{CBO}	50	V				0.5±0.1	0.4±0.1
Collector-emitter voltage (Base open)	V _{CEO}	40	V					
Emitter-base voltage (Collector open)	V _{EBO}	5	V			0.8 C	2 3 1 2 2 2	til0.
Collector current	I _C	1.5	A	_				Emitter
Peak collector current	I _{CP}	3	А			2.5±0.2	2.5±0,2	2: Collector
Collector power dissipation	Pc	1.5	W				in	3: Base
Junction temperature	Tj	150	°C				<u>ં પ્ર</u>	
Storage temperature	T _{stg}	-55 to +150	°C			N AL	'int	

Electrical Characteristics $T_a = 25^{\circ}C$ $\pm 3^{\circ}C$

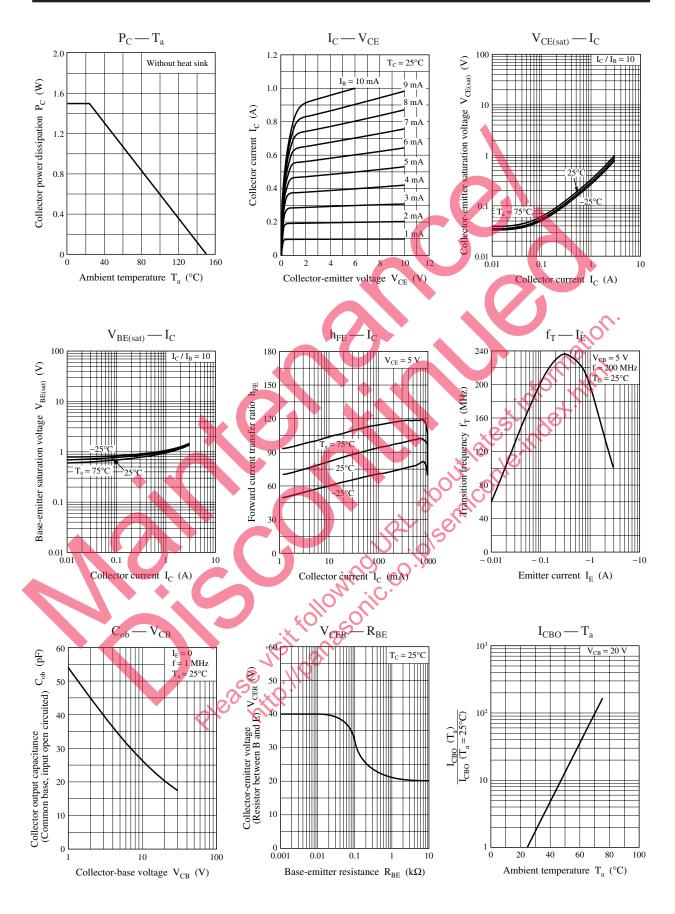
Storage temperature	I stg	-55 to +150 °C	2	\mathcal{N}				
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$								
Parameter	Symbol	Conditions •	Min	Тур	Max	Unit		
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 1 \text{ mA}, I_{\rm E} = 0$	50			V		
Collector-emitter voltage (Base open)	VCEO	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	40			V		
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CE} = 20 \text{ V}, I_E = 0$			1	μΑ		
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ		
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} \neq 5$ V, $I_C = 0$			10	μΑ		
Forward current transfer ratio *	DEE	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 1 \text{ A}$	50		220	_		
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 2 {\rm A}, I_{\rm B} = 0.2 {\rm A}$			1	V		
Base-emitter saturation voltage	V _{BE(sat)}	$I_{\rm C} = 2 {\rm A}, I_{\rm B} = 0.2 {\rm A}$			1.5	V		
Transition frequency	f _T	$V_{CB} = 5 \text{ V}, I_E = -0.5 \text{ A}, f = 200 \text{ MHz}$		150		MHz		
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		35		pF		

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Rank classification

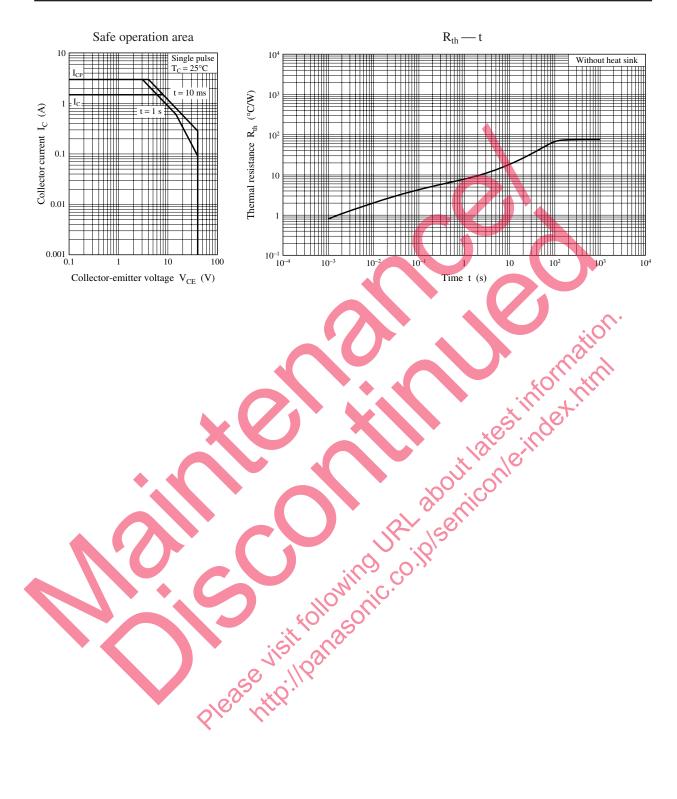
Rank	Р	Q	R		
h _{FE}	50 to 100	80 to 160	120 to 220		

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